Features

- Low-Voltage and Standard-Voltage Operation
 - $-5.0 (V_{CC} = 4.5V \text{ to } 5.5V)$
 - $-2.7 (V_{CC} = 2.7V \text{ to } 5.5V)$
 - $-2.5 (V_{CC} = 2.5V \text{ to } 5.5V)$
- 3-Wire Serial Interface
- 2 MHz Clock Rate (5V) Compatibility
- Self-Timed Write Cycle (10 ms max)
- High Reliability
 - Endurance: 1 Million Write Cycles
 - Data Retention: 100 YearsESD Protection: >4.000V
- Automotive Grade and Extended Temperature Devices Available
- 8-Pin PDIP, 8-Pin JEDEC SOIC, and 8-Pin TSSOP Packages

Description

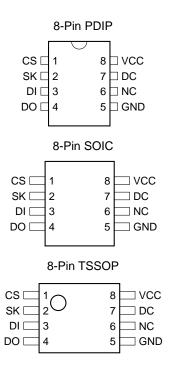
The AT93C46A provides 1024 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 64 words of 16 bits each. The device is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential. The AT93C46A is available in space saving 8-pin PDIP, 8-pin JEDEC, and 8-Pin TSSOP packages.

The AT93C46A is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a READ instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate ERASE cycle is required before WRITE. The WRITE cycle is only enabled when the part is in the ERASE/WRITE ENABLE state. When CS is brought "high" following the initiation of a WRITE cycle, the DO pin outputs the READY/BUSY status of the part.

The AT93C46A is available in 4.5V to 5.5V, 2.7V to 5.5V, and 2.5V to 5.5V versions.

Pin Configurations

Pin Name	Function
cs	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
VCC	Power Supply
NC	No Connect
DC	Don't Connect





3-Wire Serial EEPROM

1K (64 x 16)

AT93C46A

Rev. 0539C-10/98





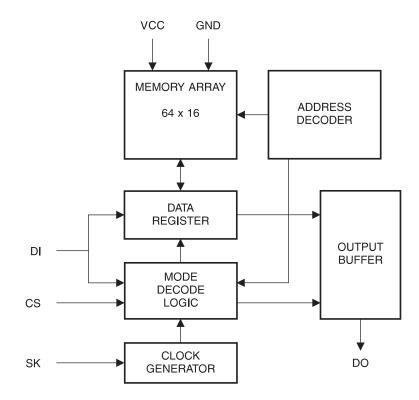
Absolute Maximum Ratings*

Operating Temperature55°C to +125°C)
Storage Temperature65°C to +150°C)
Voltage on Any Pin with Respect to Ground1.0V to +7.0V	/
Maximum Operating Voltage	/
DC Output Current	4

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Block Diagram



Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25$ °C, f = 1.0 MHz, $V_{CC} = +5.0$ V (unless otherwise noted).

Symbol	Test Conditions	Max	Units	Conditions
C _{OUT}	Output Capacitance (DO)	5	pF	$V_{OUT} = 0V$
C _{IN}	Input Capacitance (CS, SK, DI)	5	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: T_{AI} = -40°C to +85°C, V_{CC} = +2.5V to +5.5V, T_{AC} = 0°C to +70°C, V_{CC} = +2.5V to +5.5V (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
V _{CC1}	Supply Voltage			1.8		5.5	V
V _{CC2}	Supply Voltage			2.5		5.5	V
V _{CC3}	Supply Voltage			2.7		5.5	V
V _{CC4}	Supply Voltage			4.5		5.5	V
	Committee Comment	V 5.0V	READ at 1.0 MHz		0.5	2.0	mA
I _{CC}	Supply Current	$V_{CC} = 5.0V$	WRITE at 1.0 MHz		0.5	2.0	mA
I _{SB1}	Standby Current	V _{CC} = 2.5V	CS = 0V		14.0	20.0	μA
I _{SB2}	Standby Current	V _{CC} = 2.7V	CS = 0V		14.0	20.0	μA
I _{SB3}	Standby Current	V _{CC} = 5.0V	CS = 0V		35.0	50.0	μA
I _{IL}	Input Leakage	$V_{IN} = 0V \text{ to } V_{CC}$			0.1	1.0	μA
I _{OL}	Output Leakage	$V_{IN} = 0V \text{ to } V_{CC}$			0.1	1.0	μA
V _{IL1} ⁽¹⁾ V _{IH1} ⁽¹⁾	Input Low Voltage Input High Voltage	4.5V ≤ V _{CC} ≤ 5.5V		-0.6 2.0		0.8 V _{CC} + 1	V
V _{IL2} ⁽¹⁾ V _{IH2} ⁽¹⁾	Input Low Voltage Input High Voltage	1.8V ≤ V _{CC} ≤ 2.7V		-0.6 V _{CC} x 0.7		V _{CC} x 0.3 V _{CC} + 1	V
V _{OL1}	Output Low Voltage	4.5)/ 4.3/	I _{OL} = 2.1 mA			0.4	V
V _{OH1}	Output High Voltage	$4.5V \le V_{CC} \le 5.5V$	I _{OH} = -0.4 mA	2.4			V
V _{OL2}	Output Low Voltage	4.01/21/2021/	I _{OL} = 0.15 mA			0.2	V
V _{OH2}	Output High Voltage	$1.8V \le V_{CC} \le 2.7V$	I _{OH} = -100 μA	V _{CC} - 0.2			V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.





AC Characteristics

Applicable over recommended operating range from T_A = -40°C to + 85°C, V_{CC} = +2.5V to + 5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
f _{SK}	SK Clock Frequency	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$,	0 0 0 0		2 1 0.5 0.25	MHz
t _{SKH}	SK High Time	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$,	250 250 500 1000			ns
t _{SKL}	SK Low Time	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$,	250 250 500 1000			ns
t _{CS}	Minimum CS Low Time	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$,	250 250 500 1000			ns
t _{css}	CS Setup Time	Relative to SK	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	50 50 100 200			ns
t _{DIS}	DI Setup Time	Relative to SK	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	100 100 200 400			ns
t _{CSH}	CS Hold Time	Relative to SK		0			ns
t _{DIH}	DI Hold Time	Relative to SK	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	100 100 200 400			ns
t _{PD1}	Output Delay to '1'	AC Test	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$			250 250 500 1000	ns
t _{PD0}	Output Delay to '0'	AC Test	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$			250 250 500 1000	ns
t _{SV}	CS to Status Valid	AC Test	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$			250 250 500 1000	ns
t _{DF}	CS to DO in High Impedance	AC Test CS = V _{IL}	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$			100 100 200 400	ns
two	Write Cycle Time			0.1		10	ms
t _{WP}	Wille Oyole Tille		4.5V ≤ V _{CC} ≤ 5.5V		1		ms
Endurance ⁽¹⁾	5.0V, 25°C, Page Mode			1M			Write Cycle

Note: 1. This parameter is characterized and is not 100% tested.

Instruction	Set for the	ΔΤ93C46Δ
เมอน นษนษม	oet ioi nie	ALJJUTUA

			Address	
Instruction	SB	Op Code	x 16	Comments
READ	1	10	A ₅ - A ₀	Reads data stored in memory, at specified address.
EWEN	1	00	11XXXX	Write enable must precede all programming modes.
ERASE	1	11	A ₅ - A ₀	Erase memory location A _n - A ₀ .
WRITE	1	01	A ₅ - A ₀	Writes memory location A _n - A ₀ .
ERAL	1	00	10XXXX	Erases all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V.
WRAL	1	00	01XXXX	Writes all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V.
EWDS	1	00	00XXXX	Disables all programming instructions.

Functional Description

The AT93C46A is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a Start Bit (logic "1") followed by the appropriate Op Code and the desired memory Address location.

READ (READ): The Read (READ) instruction contains the Address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 16-bit data output string.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the Erase/Write Enable state, programming remains enabled until an Erase/Write Disable (EWDS) instruction is executed or V_{CC} power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 16 bits of data to be written into the specified memory location. The self-timed programming cycle, t_{WP} , starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A READY/BUSY status cannot be obtained if the CS is brought high after the end of the self-timed programming cycle, t_{WP}

ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The ERAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The WRAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

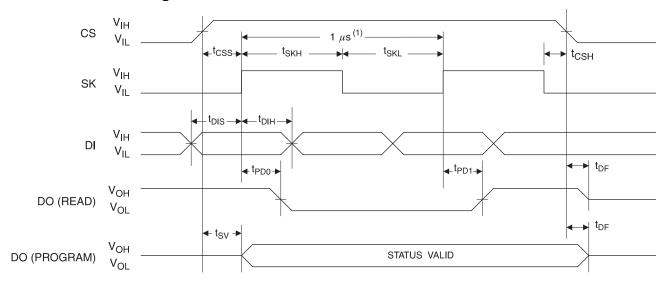
ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the READ instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.





Timing Diagrams

Synchronous Data Timing

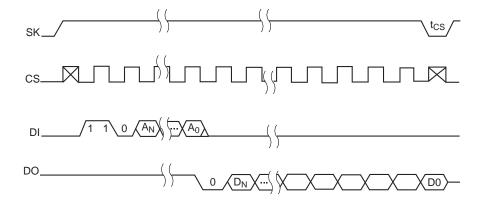


Note: 1. This is the minimum SK period.

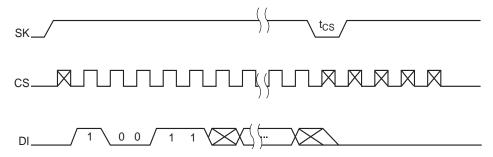
Organization Key for Timing Diagrams

	AT93C46A	
I/O	x 16	
A _N	A_5	
D _N	D ₁₅	

READ Timing

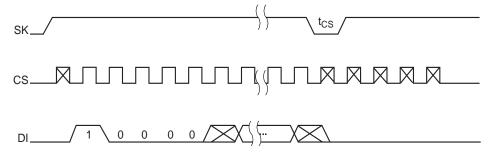


EWEN Timing⁽¹⁾



Note: 1. Requires a minimum of nine clock cycles.

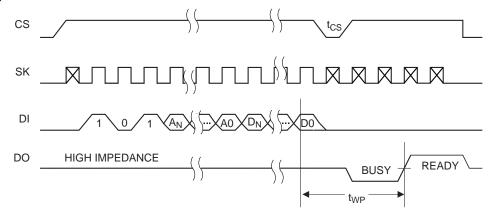
EWDS Timing⁽¹⁾



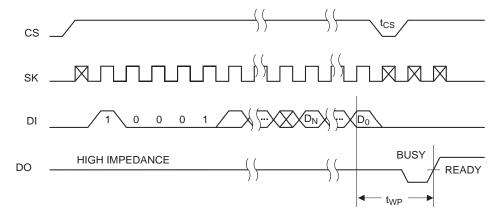
Note: 1. Requires a minimum of nine clock cycles.



WRITE Timing



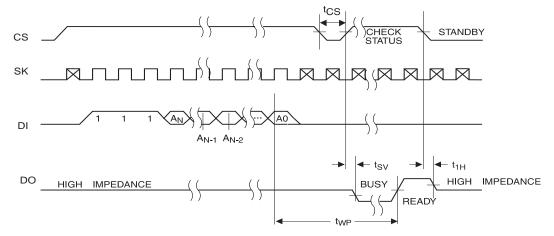
WRAL Timing⁽¹⁾⁽²⁾



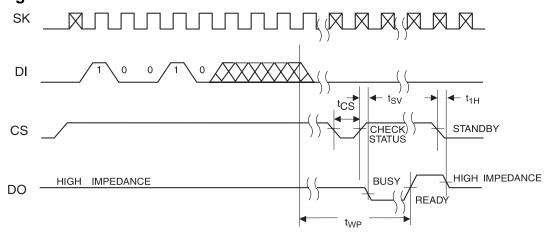
Notes: 1. Valid only at $V_{CC} = 4.5V$ to 5.5V.

2. Requires a minimum of nine clock cycles.

ERASE Timing



TERAL Timing⁽¹⁾



Note: 1. Valid only at $V_{CC} = 4.5V$ to 5.5V.



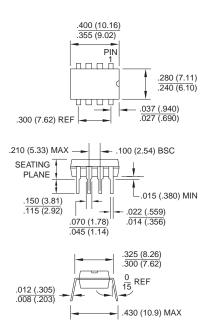
Ordering Information

t _{WP} (max) (ms)	I _{CC} (max) (μA)	I _{SB} (max) (μΑ)	f _{MAX} (kHz)	Ordering Code	Package	Operation Range
10	2000	50.0	2000	AT93C46A-10PC	8P3	Commercial
				AT93C46A-10SC	8S1	(0°C to 70°C)
				AT93C46A-10TC	8T	
10	2000	50.0	2000	AT93C46A-10PI	8P3	Industrial
				AT93C46A-10SI	8S1	(-40°C to 85°C)
				AT93C46A-10TI	8T	
10	800	20.0	1000	AT93C46A-10PC-2.7	8P3	Commercial
				AT93C46A-10SC-2.7	8S1	(0°C to 70°C)
				AT93C46A-10TC-2.7	8T	
10	800	20.0	1000	AT93C46A-10PI-2.7	8P3	Industrial
				AT93C46A-10SI-2.7	8S1	(-40°C to 85°C)
				AT93C46A-10TI-2.7	8T	
10	600	20.0	500	AT93C46A-10PC-2.5	8P3	Commercial
				AT93C46A-10SC-2.5	8S1	(0°C to 70°C)
				AT93C46A-10TC-2.5	8T	
10	600	20.0	500	AT93C46A-10PI-2.5	8P3	Industrial
				AT93C46A-10SI-2.5	8S1	(-40°C to 85°C)
				AT93C46A-10TI-2.5	8T	

	Package Type				
8P3	8-Lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)				
8S1	8-Lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)				
8T	8-Lead, 0.170" Wide, Thin Small Outline Package (TSSOP)				
	Options				
Blank	Standard Device (4.5V to 5.5V)				
-2.7	Low Voltage (2.7V to 5.5V)				
-2.5	Low Voltage (2.5V to 5.5V)				

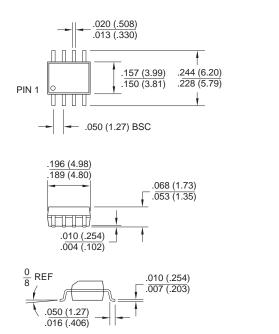
Packaging Information

8P3, 8-Lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-001 BA



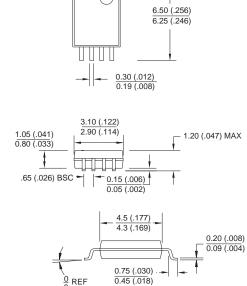
8S1, 8-Lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)

Dimensions in Inches and (Millimeters)



8T, 8-Lead, 0.170" Wide, Thin Small Outline Package (TSSOP)

Dimensions in Millimeters and (Inches)*







Atmel Headquarters

Corporate Headquarters

2325 Orchard Parkway San Jose, CA 95131 TEL (408) 441-0311 FAX (408) 487-2600

Europe

Atmel U.K., Ltd.
Coliseum Business Centre
Riverside Way
Camberley, Surrey GU15 3YL
England
TEL (44) 1276-686677
FAX (44) 1276-686697

Asia

Atmel Asia, Ltd.
Room 1219
Chinachem Golden Plaza
77 Mody Road
Tsimshatsui East
Kowloon, Hong Kong
TEL (852) 27219778
FAX (852) 27221369

Japan

Atmel Japan K.K. Tonetsu Shinkawa Bldg., 9F 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan TEL (81) 3-3523-3551 FAX (81) 3-3523-7581

Atmel Operations

Atmel Colorado Springs

1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 TEL (719) 576-3300 FAX (719) 540-1759

Atmel Rousset

Zone Industrielle 13106 Rousset Cedex, France TEL (33) 4 42 53 60 00 FAX (33) 4 42 53 60 01

> Fax-on-Demand North America: 1-(800) 292-8635 International: 1-(408) 441-0732

e-mail literature@atmel.com

Web Site http://www.atmel.com

BBS 1-(408) 436-4309

© Atmel Corporation 1998.

Atmel Corporation makes no warranty for the use of its products, other than those expressly contained in the Company's standard warranty which is detailed in Atmel's Terms and Conditions located on the Company's website. The Company assumes no responsibility for any errors which may appear in this document, reserves the right to change devices or specifications detailed herein at any time without notice, and does not make any commitment to update the information contained herein. No licenses to patents or other intellectual property of Atmel are granted by the Company in connection with the sale of Atmel products, expressly or by implication. Atmel's products are not authorized for use as critical components in life support devices or systems.

Marks bearing ® and/or ™ are registered trademarks and trademarks of Atmel Corporation.

Printed on recycled paper.